

Abstract of the Disclosure:

A Schottky diode has a Schottky junction formed by a thin metal layer and/or metal silicide layer at the top side of a doped well in a semiconductor body or substrate. In contrast 5 to the fabrication of low-impedance contacts on CMOS wells, a metal, to be precise titanium in the preferred embodiment, is applied not to a highly doped contact region but to the lightly doped semiconductor material of the doped well, for example an HV well for the fabrication of high-voltage 10 transistors.

LDP/ss